XBS053V13R-G



ETR1606-003

Schottky Barrier Diode, 500mA, 30V Type

■FEATURES

Forward Voltage : V_F=0.40V (TYP.)

Forward Current : I_{F(AV)}=500mA

Repetitive Peak Reverse Voltage: V_{RM}=30V

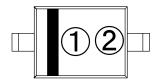
Environmentally Friendly : EU RoHS Compliant, Pb Free

■ ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	RATINGS	UNIT	
Repetitive Peak Voltage	VRM	30	V	
Reverse Voltage (DC)	VR	20	V	
Forward Current (Average)	I F(AV)	500	mA	
Non Continuous	IFSM	5	А	
Forward Surge Current ^{*1}	IF5M	5		
Junction Temperature	Tj	125	°C	
Storage Temperature Range	Tstg	-55~+150	°C	

^{*1:} Non continuous high amplitude 60Hz half-sine wave.

■MARKING RULE

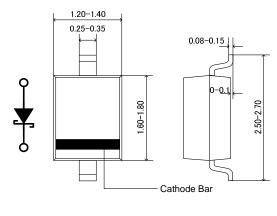


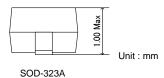
- ①: 0 (Product Number)
- 2: Assembly Lot Number

■APPLICATIONS

- Rectification
- Protection against reverse connection of battery

■PACKAGING INFORMATION





■ PRODUCT NAME

PRODUCT NAME	DEVICE ORIENTATION		
XBS053V13R	SOD-323A		
XBS053V13R-G	SOD-323A(Halogen & Antimony free)		

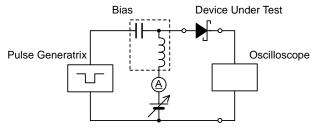
^{*} The "-G" suffix indicates that the products are Halogen and Antimony free as well as being fully RoHS compliant.

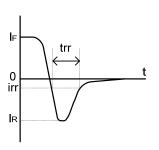
■ELECTRICAL CHARACTERISTICS

Ta=25°C

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
PARAWETER			MIN.	TYP.	MAX.	UNIT
Forward Voltage	VF1	I _F =100mA	-	0.28	-	V
	VF2	I _F =500mA	1	0.40	0.47	V
Reverse Current	lr	V _R =20V	1	ı	100	μΑ
Inter-Terminal Capacity	Ct	V _R =10V , f=1MHz	-	12	-	pF
Reverse Recovery Time*2	trr	I _F =I _R =10mA , irr=1mA	-	8	-	ns

^{*2 :} trr measurement circuit

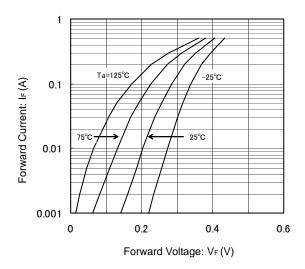




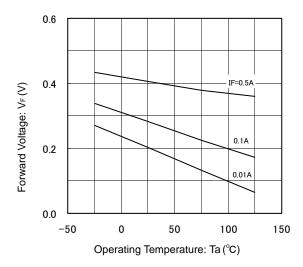
^{*} The device orientation is fixed in its embossed tape pocket.

■TYPICAL PERFORMANCE CHARACTERISTICS

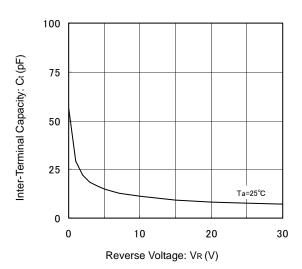
(1) Forward Current vs. Forward Voltage



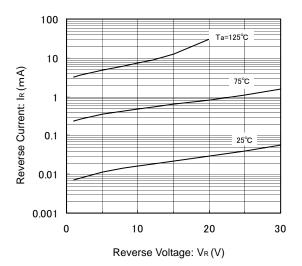
(3) Forward Voltage vs. Operating Temperature



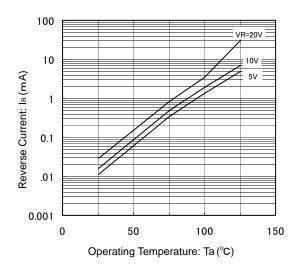
(5) Inter-Terminal Capacity vs. Reverse Voltage



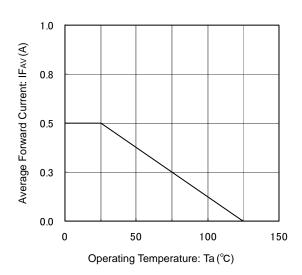
(2) Reverse Current vs. Reverse Voltage



(4) Reverse Current vs. Operating Temperature



(6) Average Forward Current vs. Operating Temperature



- 1. The products and product specifications contained herein are subject to change without notice to improve performance characteristics. Consult us, or our representatives before use, to confirm that the information in this datasheet is up to date.
- 2. We assume no responsibility for any infringement of patents, patent rights, or other rights arising from the use of any information and circuitry in this datasheet.
- 3. Please ensure suitable shipping controls (including fail-safe designs and aging protection) are in force for equipment employing products listed in this datasheet.
- 4. The products in this datasheet are not developed, designed, or approved for use with such equipment whose failure of malfunction can be reasonably expected to directly endanger the life of, or cause significant injury to, the user.
 - (e.g. Atomic energy; aerospace; transport; combustion and associated safety equipment thereof.)
- Please use the products listed in this datasheet within the specified ranges.
 Should you wish to use the products under conditions exceeding the specifications, please consult us or our representatives.
- 6. We assume no responsibility for damage or loss due to abnormal use.
- All rights reserved. No part of this datasheet may be copied or reproduced without the prior permission of TOREX SEMICONDUCTOR LTD.

TOREX SEMICONDUCTOR LTD.